



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The is Designed for

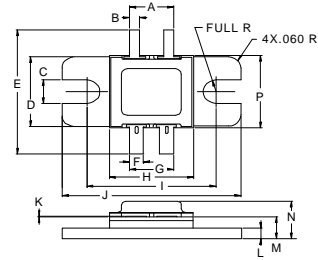
FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	21.6 A
V_{CB0}	65 V
V_{CES}	65 V
V_{EBO}	3.5 V
P_{DISS}	875 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.2 °C/W

PACKAGE STYLE .400 BAL FLG(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.210 / 5.33	.230 / 5.84
B	.045 / 1.14	.055 / 1.40
C	.125 / 3.18	.135 / 3.43
D	.380 / 9.65	.390 / 9.91
E	.770 / 19.56	.830 / 21.08
F	.070 / 1.78	.080 / 2.03
G	.215 / 5.46	.235 / 5.97
H	.420 / 10.67	.430 / 10.92
I	.645 / 16.38	.655 / 16.64
J	.895 / 22.73	.905 / 22.99
K	.002 / 0.05	.006 / 0.15
L	.058 / 1.47	.065 / 1.65
M	.115 / 2.92	.130 / 3.30
N		.230 / 5.84
P	.395 / 10.03	.405 / 10.29

ORDER CODE: ASI10686

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 50 mA	65			V
BV_{CES}	I _C = 50 mA	65			V
BV_{CEO}	I _C = 50 mA	28			V
BV_{EBO}	I _E = 10 mA	3.5			V
I_{CES}	V _{CE} = 30 V			7.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 5.0 A	10		100	---
P_G	V _{CE} = 40 V P _{OUT} = 300 W f = 425 MHz	9.5			dB
η_C		55			%

ADVANCED SEMICONDUCTOR, INC.

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REV. A

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Specifications are subject to change without notice.